

APM2324A

N-Channel Enhancement Mode MOSFET

Feature

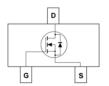
- 20V/3A, $R_{DS(ON)} = 80m\Omega(MAX)$ @ $V_{GS} = 4.5V$. $R_{DS(ON)} = 90m\Omega(MAX)$ @ $V_{GS} = 2.5V$.
- Super High dense cell design for extremely low RDS(ON).
- Reliable and Rugged.
- SC-59 for Surface Mount Package.

Applications

- Power Management
- Portable Equipment and Battery Powered Systems.







Absolute Maximum Ratings TA=25°C Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±8	V
Drain Current-Continuous	I_D	3.0	A

Electrical Characteristics TA=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Тур.	Max	Units		
Off Characteristics								
Drain to Source Breakdown Voltage	BVDSS	VGS=0V, ID=250μA	20	-	-	V		
Zero-Gate Voltage Drain Current	IDSS	VDS=12V, VGS=0V	-	-	1	μΑ		
Gate Body Leakage Current, Forward	IGSSF	VGS=8V, VDS=0V	-	-	100	nA		
Gate Body Leakage Current, Reverse	IGSSR	VGS=-8V, VDS=0V	-	-	-100	nA		
On Characteristics								
Gate Threshold Voltage	VGS(th)	$VGS\text{=}VDS, ID\text{=}250\mu A$	0.4	-	1.3	V		
Static Drain-source	RDS(ON)	VGS =4.5V, ID =3.6A	-	70	80	mΩ		
On-Resistance		VGS =2.5V, ID =3.1A	-	75	90	mΩ		
Drain-Source Diode Characteristics and Maximum Ratings								
Drain-Source Diode Forward Voltage	VSD	VGS =0V, IS=0.94A			1.2	V		

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Typical Characteristics

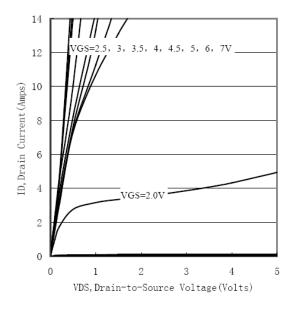


Figure 1. Output Characteristics

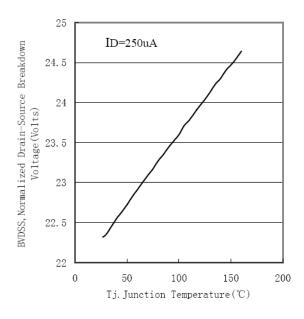


Figure 3. Breakdown Voltage Variation with Temperature

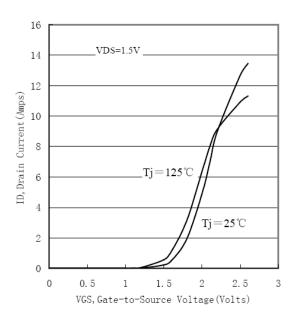


Figure 2. Transfer Characteristics

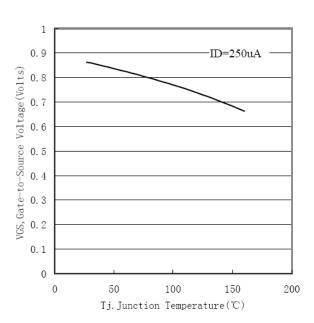
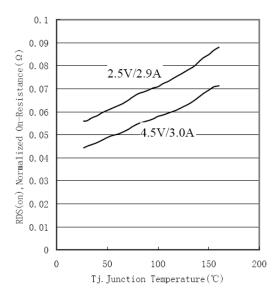


Figure 4. Gate Threshold Variation with Temperature





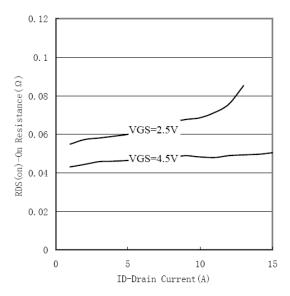
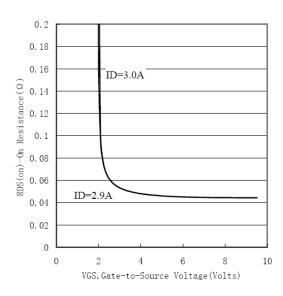
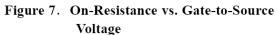


Figure 5. On-Resistance Variation with Temperature

Figure 6. On-Resistance vs. Drain Current





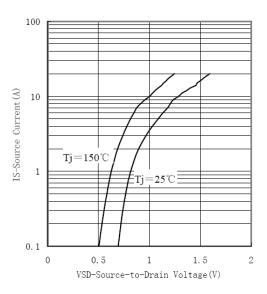


Figure 8. Source-Drain Diode Forward Voltage